

BUK7607-55B

N-channel TrenchMOS standard level FET Rev. 2 — 26 July 2011

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	55	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u> _	-	75	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	203	W
Static char	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{Figure 12}};$	-	5.8	7.1	mΩ
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	351	mJ
Dynamic cl	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A;}$ $V_{DS} = 44 \text{ V; } T_j = 25 \text{ °C;}$ see <u>Figure 13</u>	-	17	-	nC

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
		Description	Ompinica outinic	Crupino Symbol
1	G	gate		
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7607-55B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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4. Limiting values

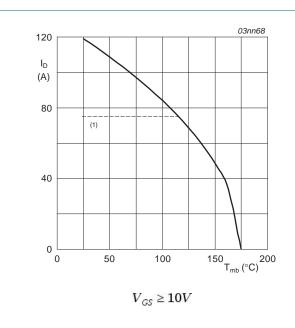
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		, ,			
Symbol	Parameter	Conditions	Mi	n Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$T_{mb} = 25 \text{ °C}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u> -	75	Α
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u> -	75	Α
		$T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V}; \text{see } \underline{\text{Figure 1}}; \text{see } \underline{\text{Figure 3}}$	[2] _	119	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see Figure 3	-	478	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	203	W
T _{stg}	storage temperature		-55	5 175	°C
Tj	junction temperature		-55	5 175	°C
Source-drai	n diode				
Is	source current	T _{mb} = 25 °C	[2] _	119	Α
			[1] _	75	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	478	Α
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 75 A; V_{sup} ≤ 55 V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	351	mJ

^[1] Continuous current is limited by package.

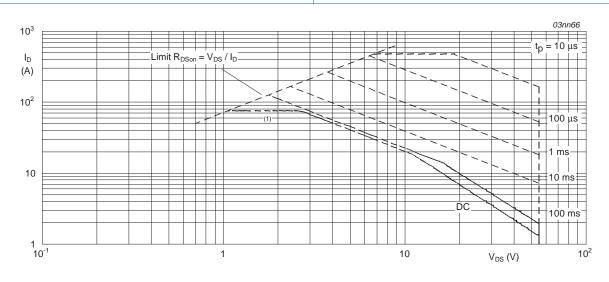
^[2] Current is limited by power dissipation chip rating.



P_{der} (%) 80 40 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

Fig 1. Normalized continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	0.74	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

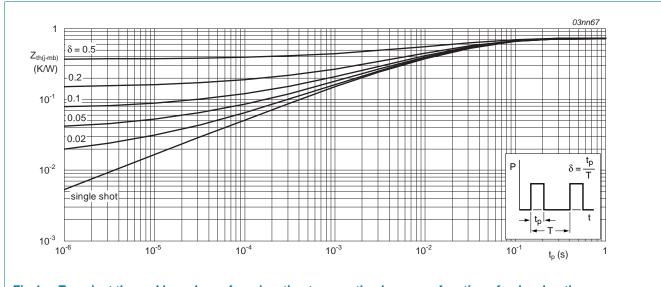


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6. Symbol	Characteristics Parameter	Conditions	Min	Typ	Max	Unit
•	racteristics	Conditions	IVIIII	Тур	IVIdX	Unit
	drain-source	I 0.25 m A · V 0.V/ T 25 ° C	FF			V
V _{(BR)DSS} drain-source breakdown voltage	$I_D = 0.25 \text{ mA; } V_{GS} = 0 \text{ V; } T_j = 25 \text{ °C}$	55	-	-	-	
. ,		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	2	3	4	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 10	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	-	0.02	1	μΑ
		V _{DS} = 55 V; V _{GS} = 0 V; T _i = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _i = 25 °C	-	2	100	nA
	- •	V _{GS} = -20 V; V _{DS} = 0 V; T _i = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A; } T_j = 175 \text{ °C;}$ see Figure 11; see Figure 12	-	-	14.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	5.8	7.1	mΩ
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{\text{ Composition}}$	-	53	-	nC
Q _{GS}	gate-source charge		-	12	-	nC
Q_{GD}	gate-drain charge		-	17	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	2820	3760	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	554	665	pF
C _{rss}	reverse transfer capacitance		-	200	274	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	24	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$; $T_j = 25 °C$	-	52	-	ns
t _{d(off)}	turn-off delay time		-	77	-	ns
t _f	fall time		-	41	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to center of die; T _i = 25 °C	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die; T _i = 25 °C	-	2.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad; T _i = 25 °C	-	7.5	-	nΗ
Source-dr	rain diode	•				
V_{SD}	source-drain voltage	$I_S = 40 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	62	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	60	-	nC

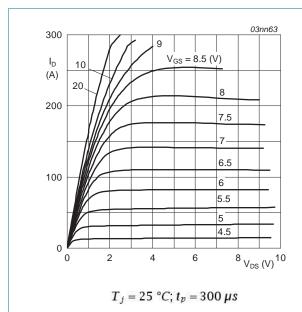


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

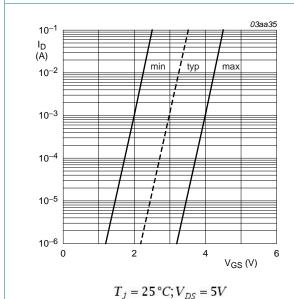
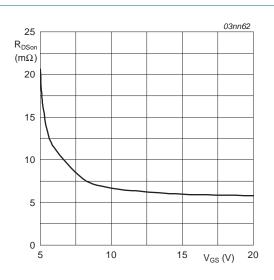
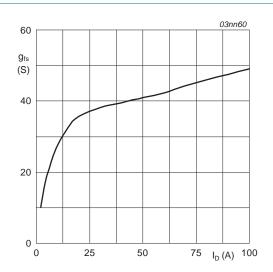


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 25A$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



$$T_j = 25^{\circ}C; V_{DS} = 25V$$

Fig 8. Forward transconductance as a function of drain current; typical values

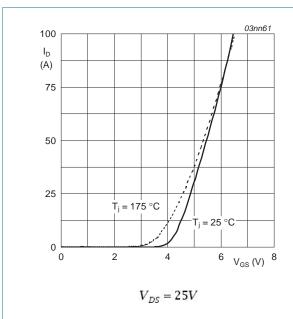


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

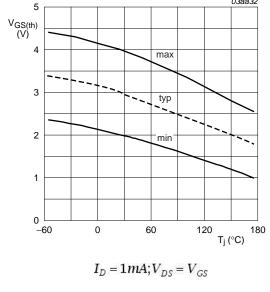


Fig 10. Gate-source threshold voltage as a function of junction temperature

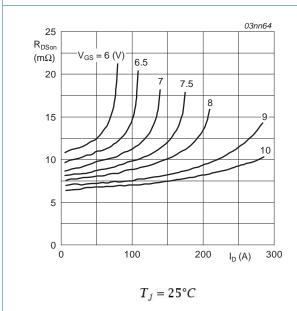


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

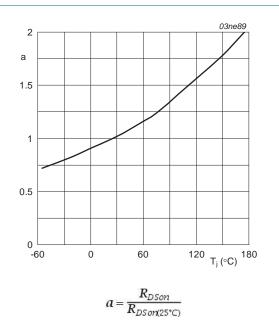
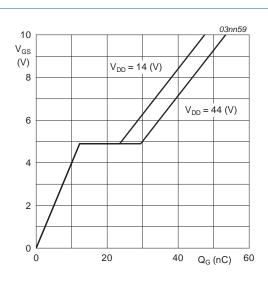
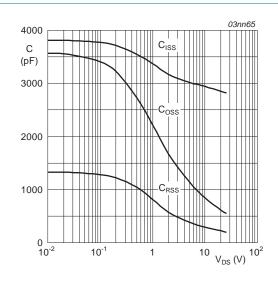


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



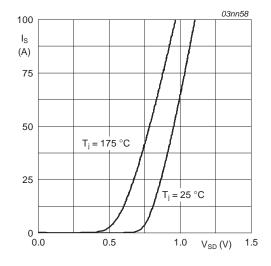
 $T_j=25^{\circ}C; I_D=25A$

Fig 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0V$

Fig 15. Source current as a function of source-drain voltage; typical values

7. Package outline

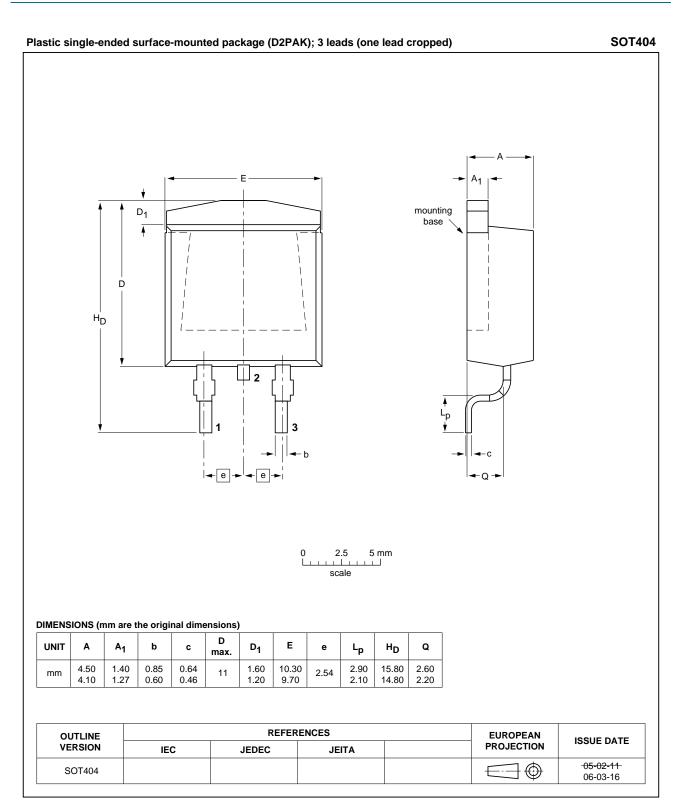


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BUK7607-55B v.2	20110726	Product data sheet	-	BUK75_7607_55B_1		
Modifications:	 Type number BUK7607-55B separated from data sheet BUK75_7607_55B_1. 					
	 The format of this of NXP Semicondo 	data sheet has been rede uctors.	signed to comply with the	e new identity guidelines		
	 Legal texts have b 	een adapted to the new o	ompany name where app	oropriate.		
BUK75_7607_55B_1 (9397 750 11235)	20030515	Product data	-	-		

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Nexperia

N-channel TrenchMOS standard level FET

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